

## PMK50XP

# P-channel TrenchMOS extremely low level FET Rev. 02 — 28 April 2010 Pr

**Product data sheet** 

### **Product profile**

#### 1.1 General description

Extremely low level P-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

#### 1.2 Features and benefits

Low conduction losses due to low on-state resistance

#### 1.3 Applications

Battery management

Load switching

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-	-20	V
I <sub>D</sub>	drain current	$T_{sp} = 25$ °C; $V_{GS} = -4.5$ V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	-7.9	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	5	W
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.8 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 9}}{\text{see } \frac{\text{Figure 10}}{\text{Figure 10}};$	-	40	50	mΩ
Dynamic ch	naracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS}$ = -4.5 V; $I_D$ = -4.7 A; $V_{DS}$ = -10 V; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	1.3	-	nC



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## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	8 <u> </u>	D
3	S	source		
4	G	gate		G L
5	D	drain	1	
6	D	drain	SOT96-1 (SO8)	S 003aaa671
7	D	drain		
8	D	drain		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMK50XP	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

#### P-channel TrenchMOS extremely low level FET

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-	-20	V
$V_{DGR}$	drain-gate voltage	$25 \text{ °C} \le T_j \le 150 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	-	-20	V
$V_{GS}$	gate-source voltage		-12	-	12	V
I <sub>D</sub>	drain current	$T_{sp} = 25 ^{\circ}\text{C}; V_{GS} = -4.5 \text{V};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	-7.9	Α
		$T_{sp}$ = 100 °C; $V_{GS}$ = -4.5 V; see <u>Figure 1</u>	-	-	-5	Α
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; $t_p \le 10 \mu s$ ; pulsed; see <u>Figure 3</u>	-	-	-31.6	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	5	W
T <sub>stg</sub>	storage temperature		-55	-	150	°C
T <sub>j</sub>	junction temperature		-55	-	150	°C
Source-drain	diode					
Is	source current	T <sub>sp</sub> = 25 °C	-	-	-4.1	Α
I <sub>SM</sub>	peak source current	$T_{sp} = 25  ^{\circ}C; t_p \le 10  \mu s; \text{ pulsed}$	-	-	-16.4	Α

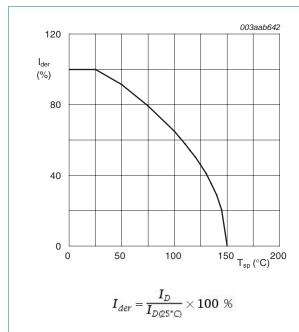


Fig 1. Normalized continuous drain current as a function of solder point temperature

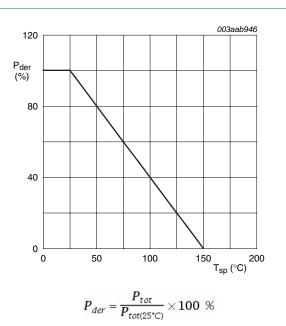
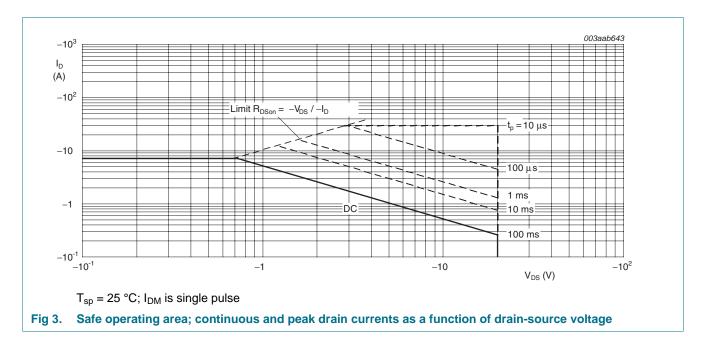


Fig 2. Normalized total power dissipation as a function of solder point temperature

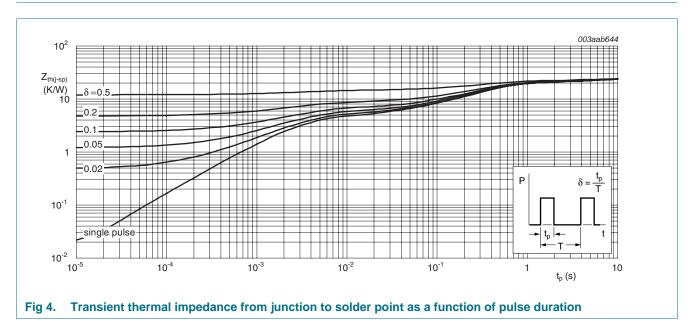
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#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Mi	lin	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 4	-		-	25	K/W



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## 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub> drain-source		$I_D = -250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	-18	-	-	V
	breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = -250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see <u>Figure 7</u> ; see <u>Figure 8</u>	-	-	-1.1	V
		$I_D = -250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 150 ^{\circ}\text{C}$ ; see <u>Figure 8</u>	-0.35	-	-	V
		$I_D = -250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 ^{\circ}\text{C}$ ; see <u>Figure 7</u> ; see <u>Figure 8</u>	-0.55	-0.75	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 70 \text{ °C}$	-	-	-5	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-10	-100	nΑ
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-10	-100	nΑ
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = -2.5 V; $I_D$ = -2.3 A; $T_j$ = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	56	70	mΩ
	$V_{GS}$ = -4.5 V; $I_D$ = -2.8 A; $T_j$ = 150 °C; see Figure 9; see Figure 10	-	64	80	mΩ	
		$V_{GS}$ = -4.5 V; $I_D$ = -2.8 A; $T_j$ = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	40	50	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = -4.7 \text{ A}$ ; $V_{DS} = -10 \text{ V}$ ; $V_{GS} = -4.5 \text{ V}$ ;	-	10	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 11; see Figure 12	-	2.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.3	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D$ = -4.7 A; $V_{DS}$ = -10 V; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-1.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1020	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	140	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	100	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -10 \text{ V}; R_L = 10 \Omega; V_{GS} = -4.5 \text{ V};$	-	8.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$	-	7.5	-	ns
d(off)	turn-off delay time		-	82	-	ns
t <sub>f</sub>	fall time		-	35	-	ns
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = -1.7 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 14	-	-0.77	-1.2	V

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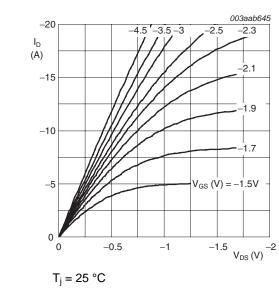


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

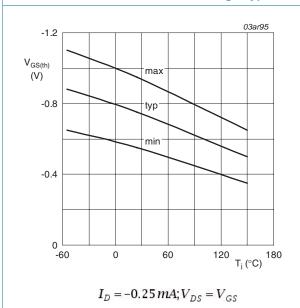
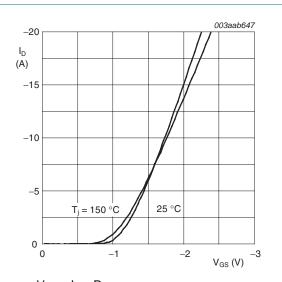
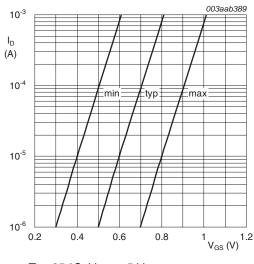


Fig 7. Gate-source threshold voltage as a function of junction temperature



 $V_{DS} > I_D \times R_{DSon}$ 

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_i = 25$  °C;  $V_{DS} = -5$  V

Fig 8. Sub-threshold drain current as a function of gate-source voltage

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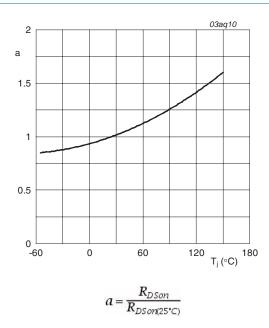
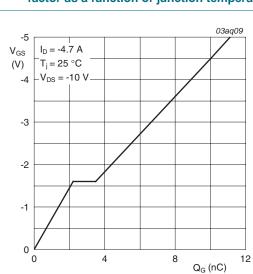


Fig 9. Normalized drain-source on-state resistance factor as a function of junction temperature



 $I_D = -4.7\,A; T_J = 25\,^{\circ}C; V_{DS} = -10\,V$  Fig 11. Gate-source voltage as a function of gate

charge; typical values

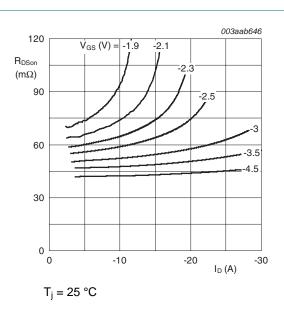


Fig 10. Drain-source on-state resistance as a function of drain current; typical values

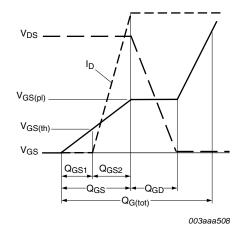


Fig 12. Gate charge waveform definitions

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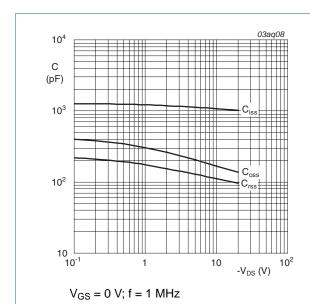


Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

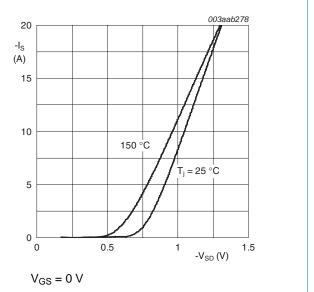


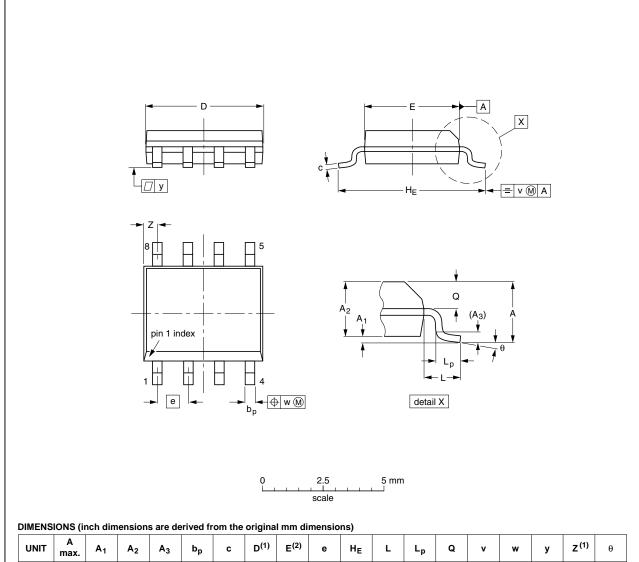
Fig 14. Source current as a function of source-drain voltage; typical values

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### 7. Package outline

#### SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	σ	v	w	у	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012				<del>99-12-27</del> 03-02-18

Fig 15. Package outline SOT96-1 (SO8)

PMK50XF

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## P-channel TrenchMOS extremely low level FET

## 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMK50XP_2	20100428	Product data sheet	-	PMK50XP_1
Modifications:	<ul> <li>Various cha</li> </ul>	nges to content.		
PMK50XP_1	20070917	Product data sheet	-	-

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Legal information

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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